

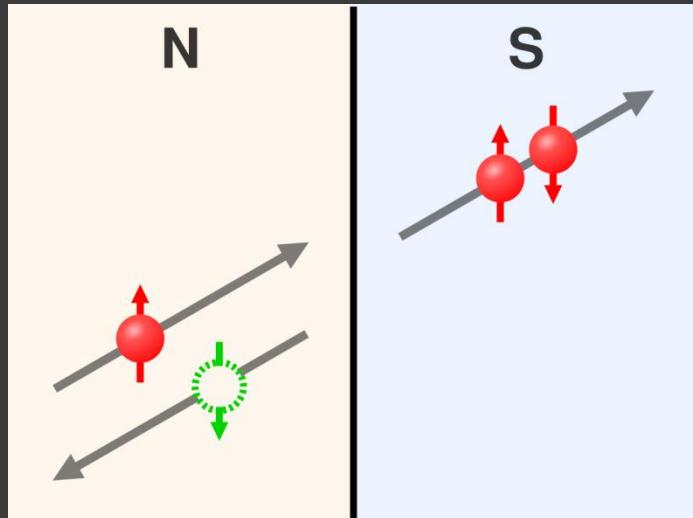
SYNTHETIC SPIN-ORBIT INTERACTION FOR MAJORANA DEVICES

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J. J. Viennot, F. Mallet, S. Rohart, A. Thiaville, A. Cottet and T. Kontos

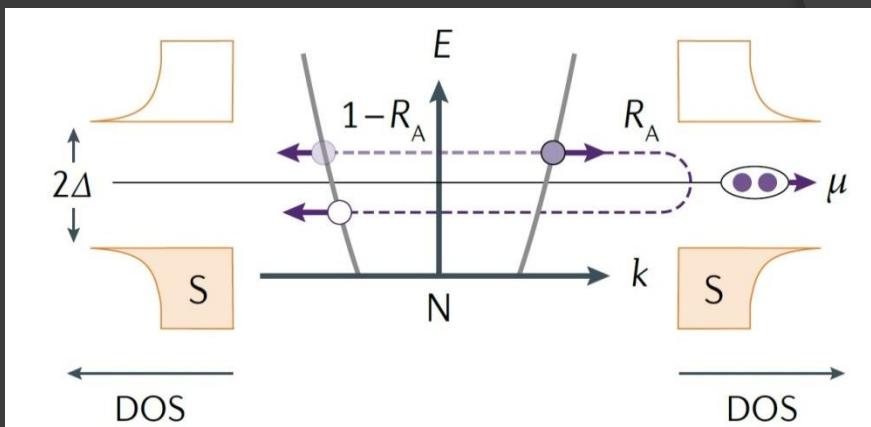
Nature Materials **18**, 1060-1064 (2019)

1. Andreev and Majorana bound states
2. Rashba spin-orbit coupling
3. Device setup
4. Induced spin-orbit interaction
5. Control device
6. Zero-bias conductance peak

Andreev reflection and Andreev bound states

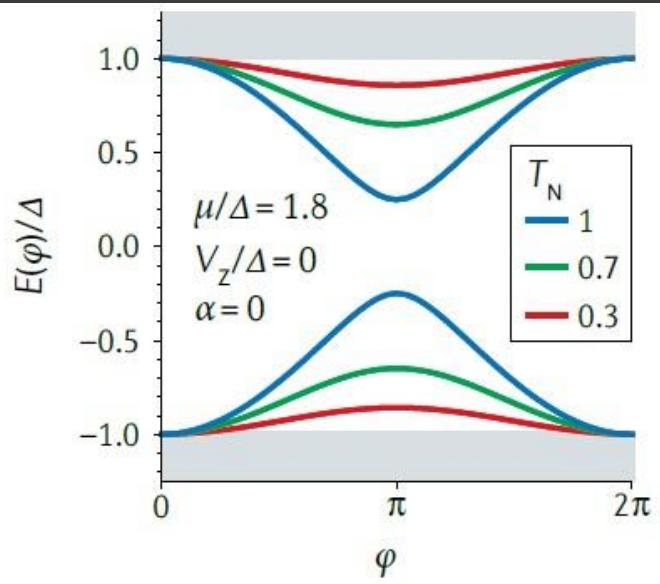
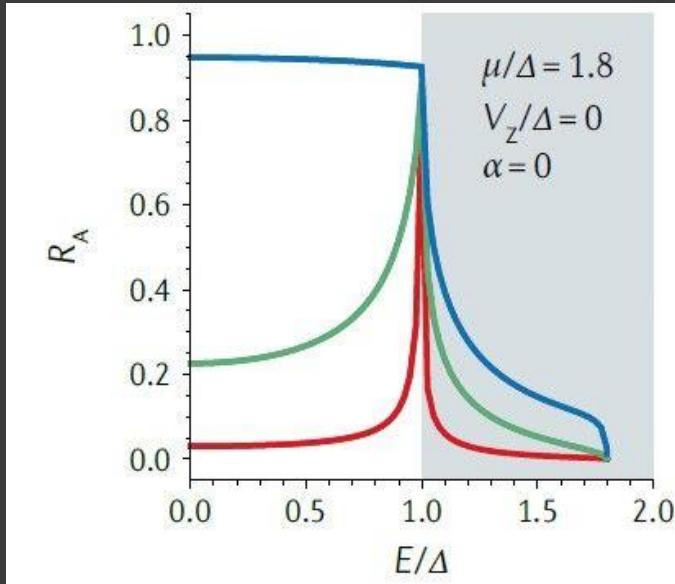


By Ilmari Karonen , <https://commons.wikimedia.org/w/index.php?curid=1065234>



Elsa Prada, Pablo San-Jose et. al.
Nature Reviews | Physics volume 2 | October 2020 | 575-594

Andreev reflection and Andreev bound states



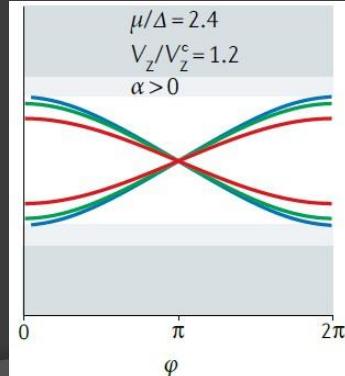
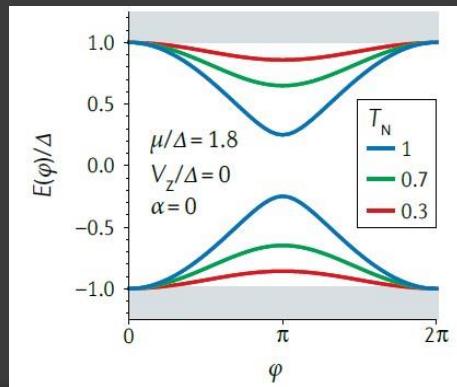
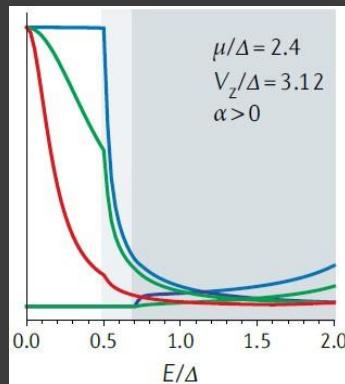
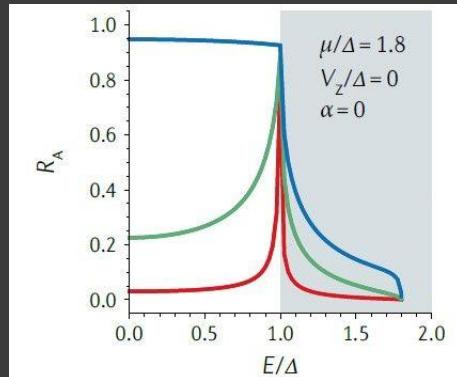
Majorana bound states

- Topologically protected zero-energy modes
- Robust against perturbations
- Exotic properties, promising for quantum computing

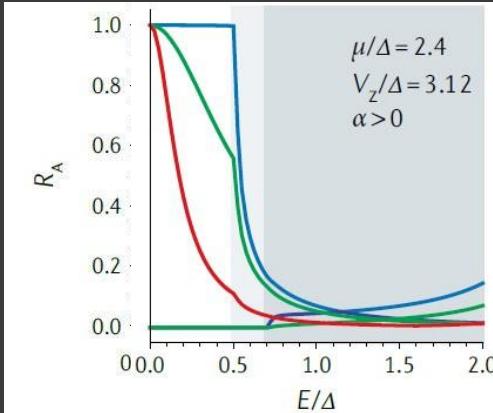
Required:

- Superconductivity
- Combination of Zeeman splitting and spin-orbit coupling
- Small chemical potential
- Comparable order of magnitude of Δ , V_z , E_{SO} , μ

Andreev to Majorana

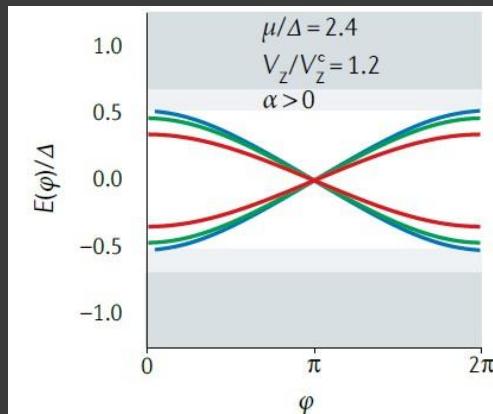


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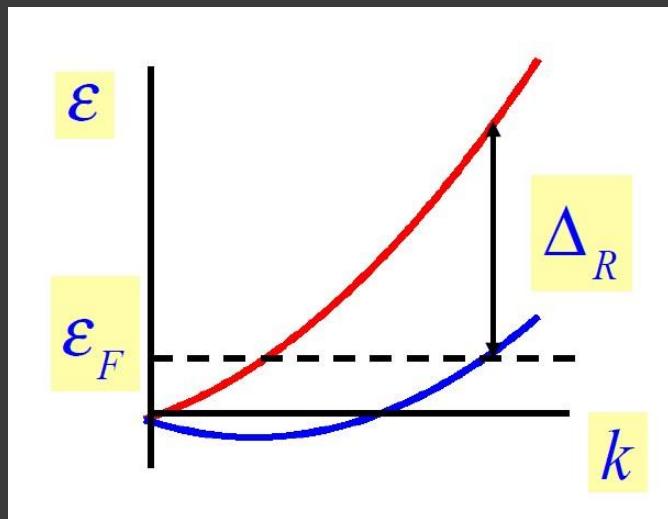
Problems:

- High Zeeman energy V_z requires high external B-field
- High external B-field suppresses superconductivity



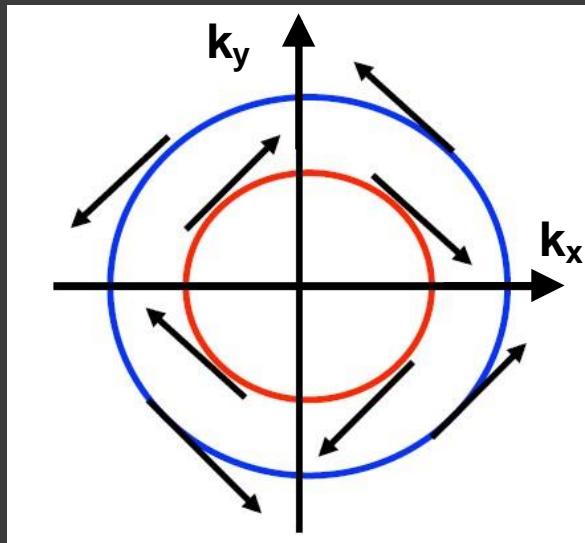
- Intrinsic spin-orbit coupling is property of the material ($\sim Z^4$)
- Too weak for low-Z-materials
- Rashba spin-orbit interaction

Rashba spin-orbit coupling

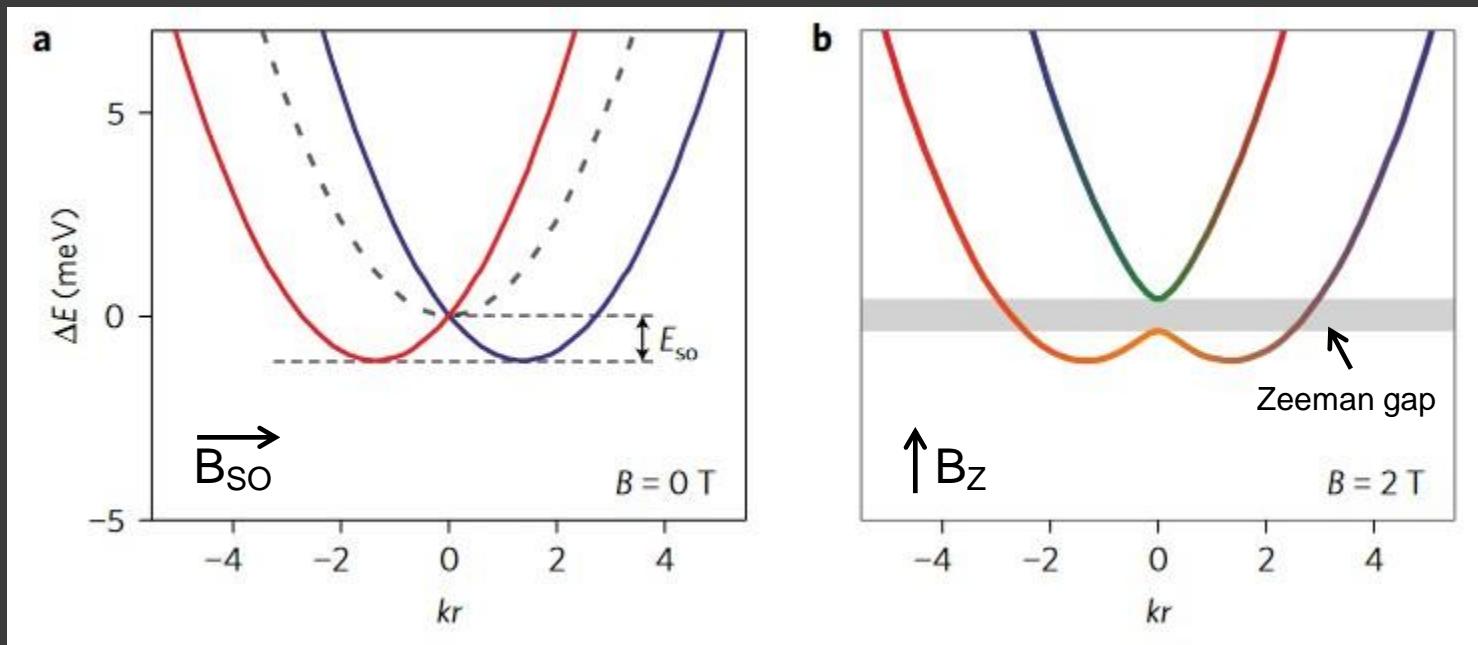


$$E_{\pm} = \frac{k^2}{2m} \pm \alpha k$$

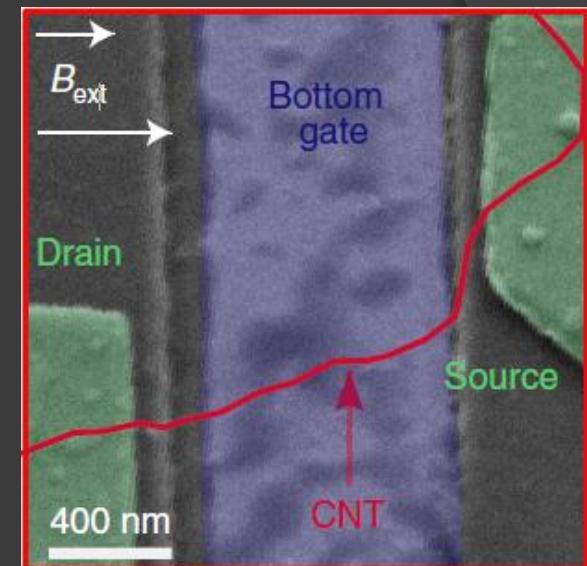
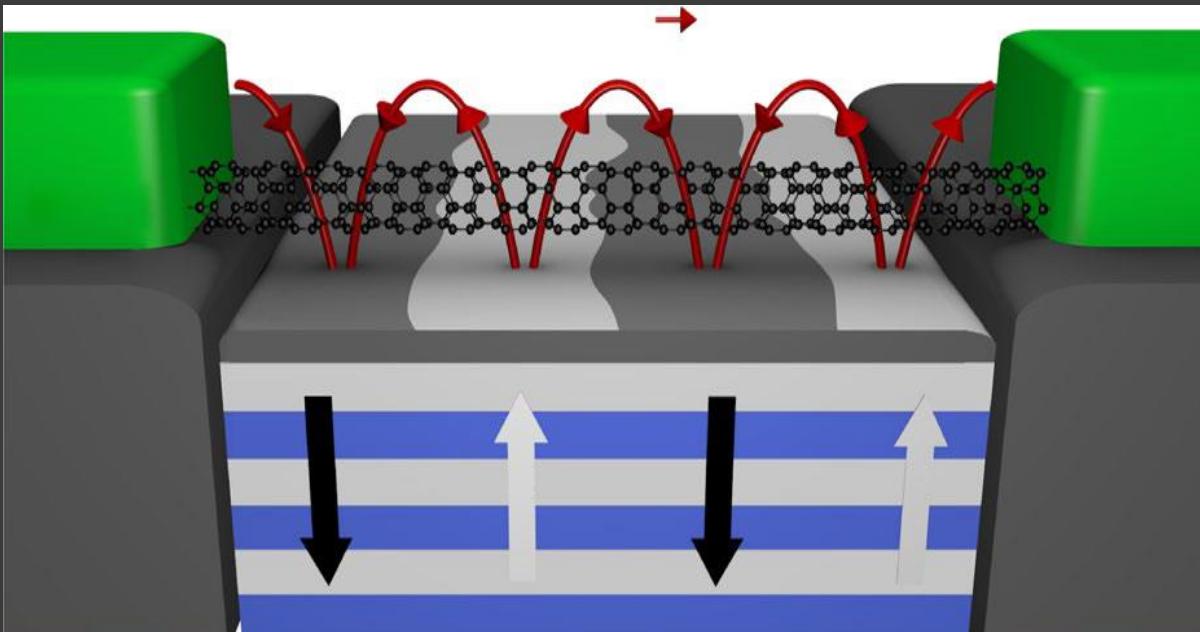
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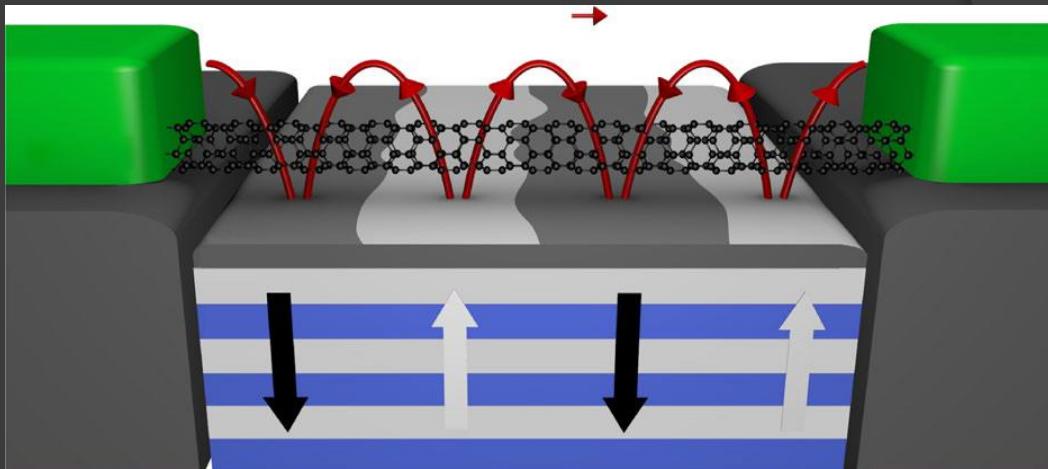
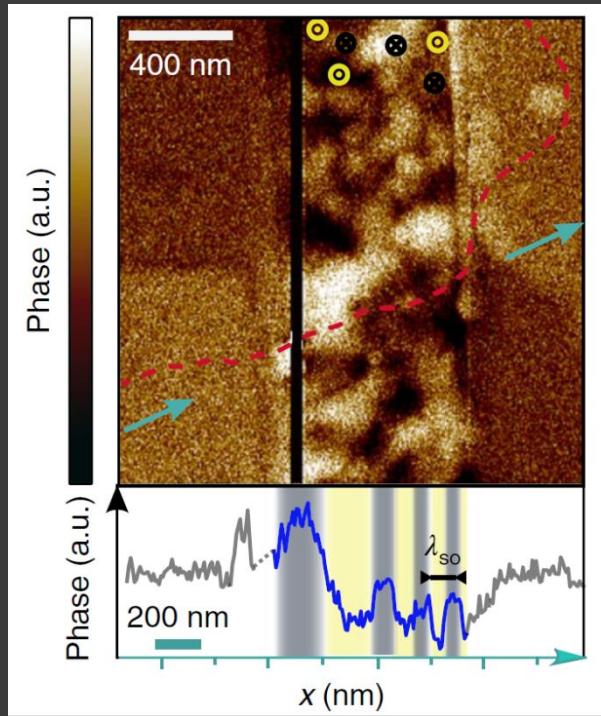
Rashba spin-orbit coupling



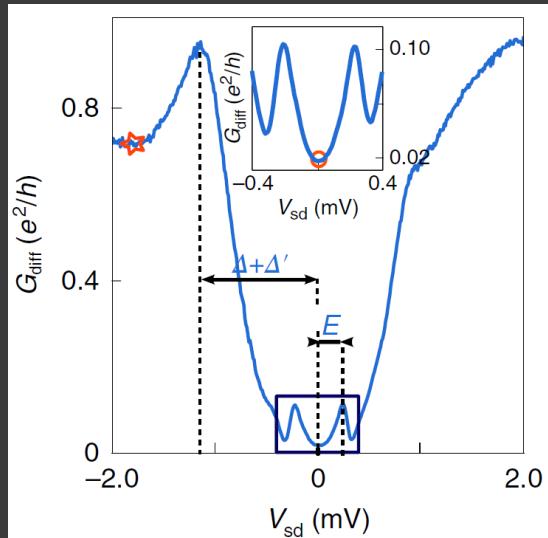
Device setup



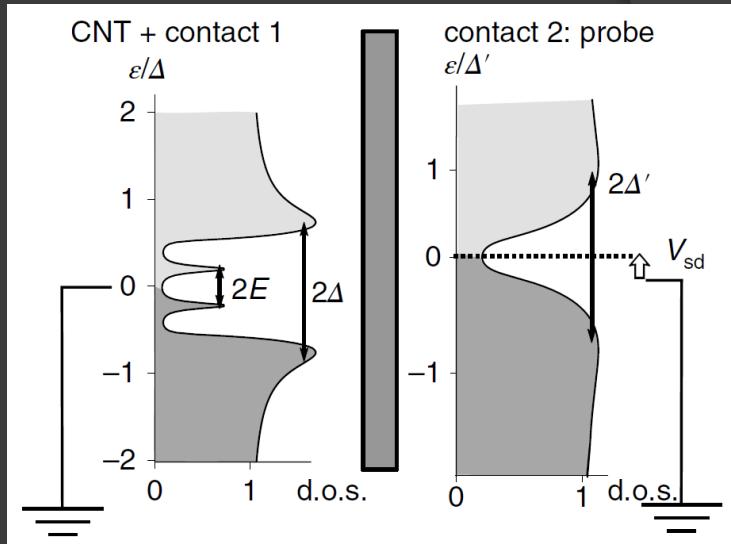
Device setup



Device setup



$$G_{diff} = \frac{dI}{dV}$$

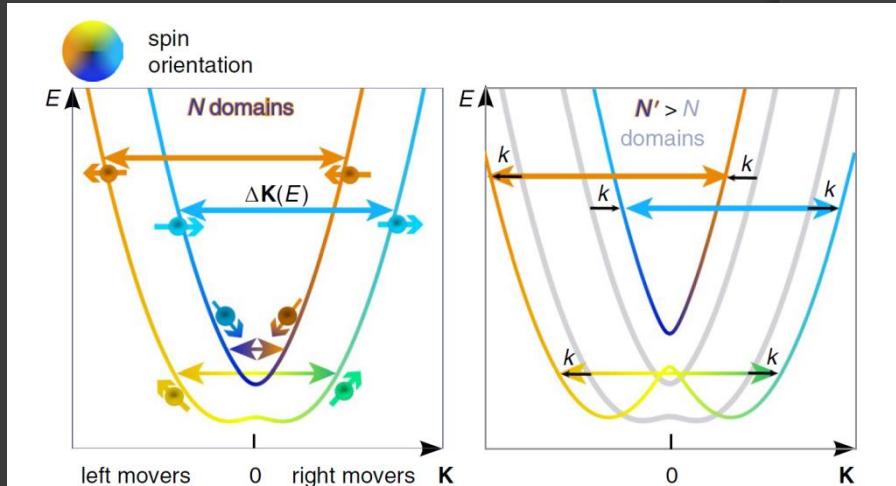


Induced spin-orbit interaction

$$\hat{H} = -\left(\frac{\hbar^2 \partial_z^2}{2m} - \mu(z)\right) + \frac{1}{2} g \mu_B \overrightarrow{B_{osc}}(z) \cdot \vec{\sigma}$$

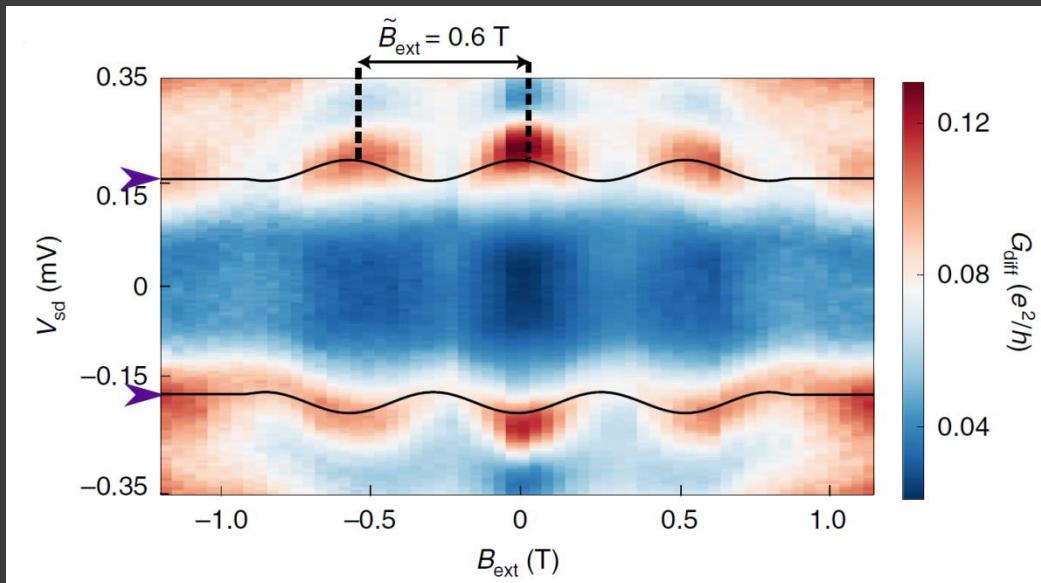
$$k_{SO} = \frac{\partial \theta}{\partial z} \quad E_{SO} = \frac{\hbar^2 k_{SO}^2}{4m}$$

$$E_{\pm}(k) = -\mu + \frac{E_{SO}}{4} + \frac{\hbar^2 k^2}{2m} \pm \sqrt{\frac{\hbar^2 k^2}{2m} E_{SO} + \left(\frac{g \mu_B B_{osc}}{2}\right)^2}$$

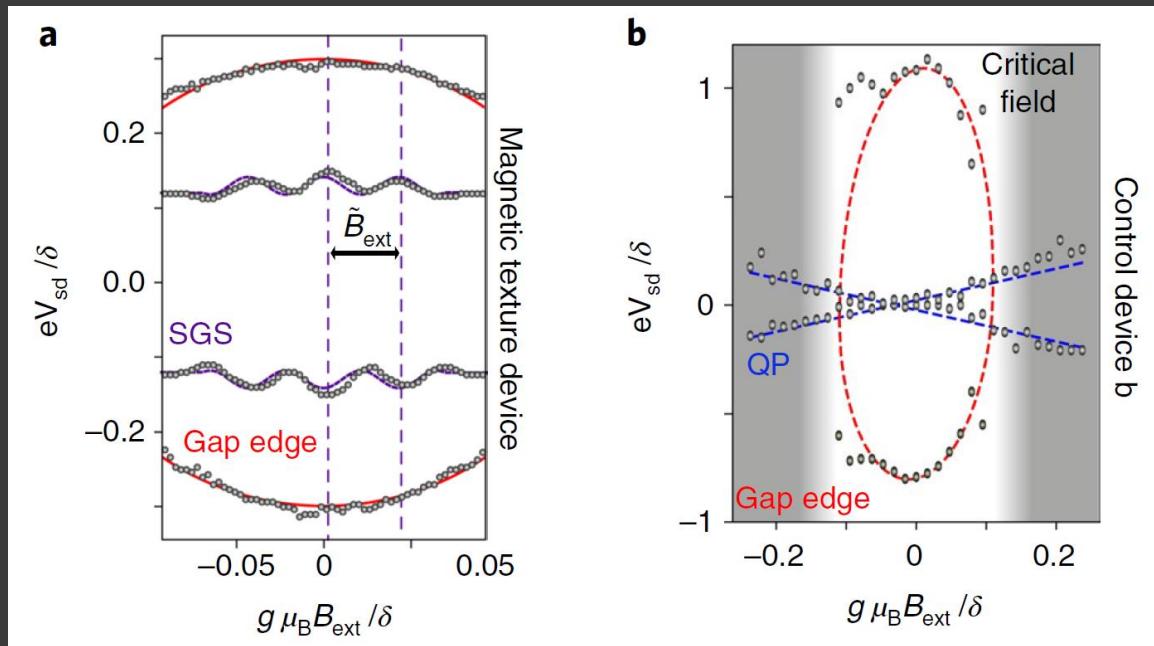


Induced spin-orbit interaction

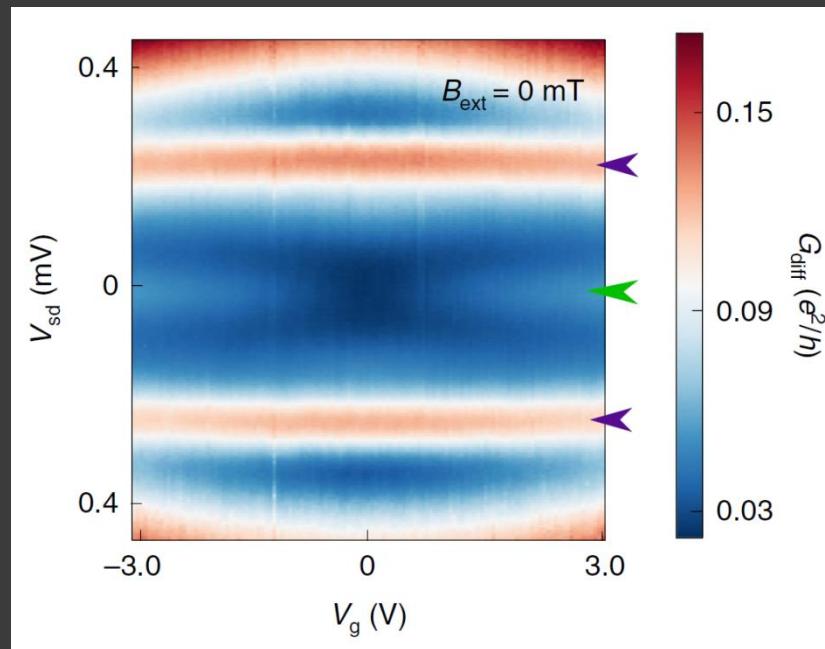
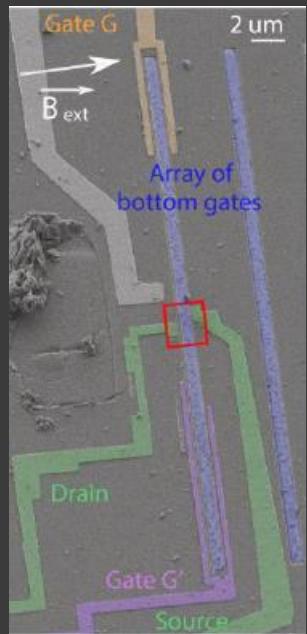
$$E_{SGS} \approx \pm E_{SGS,0} * \{1 + a * \cos[2 * \Delta K(B_{ext}) * L]\}$$



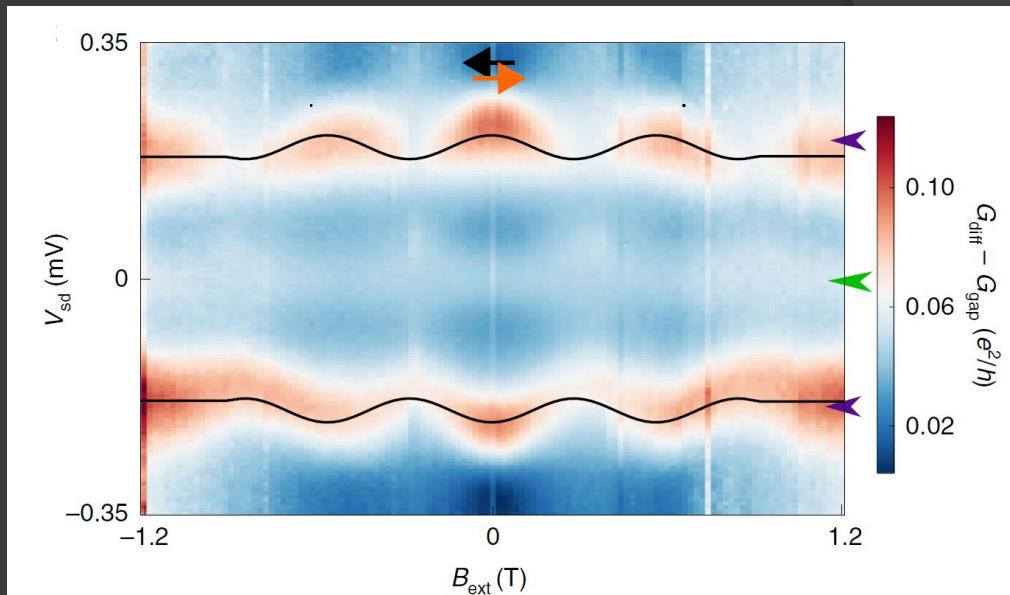
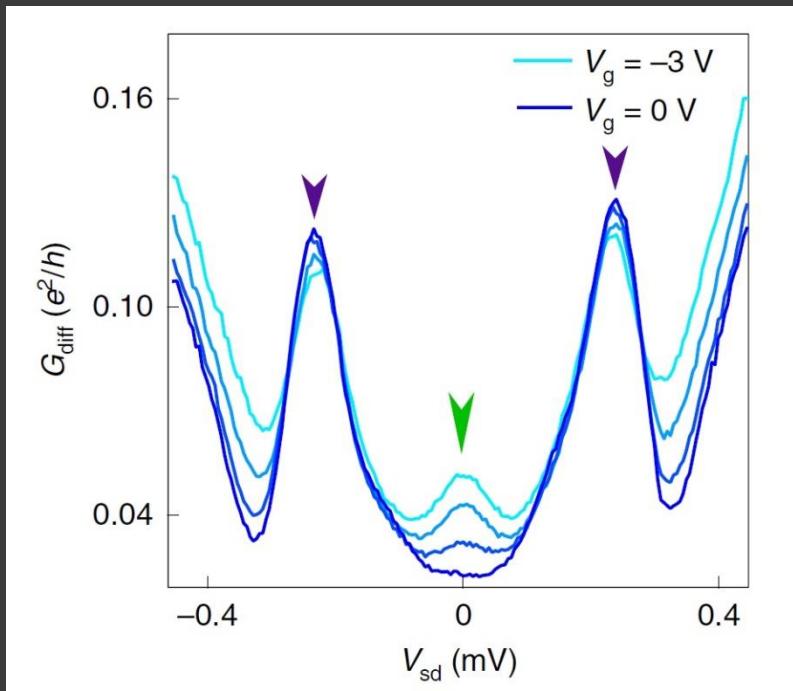
Control device



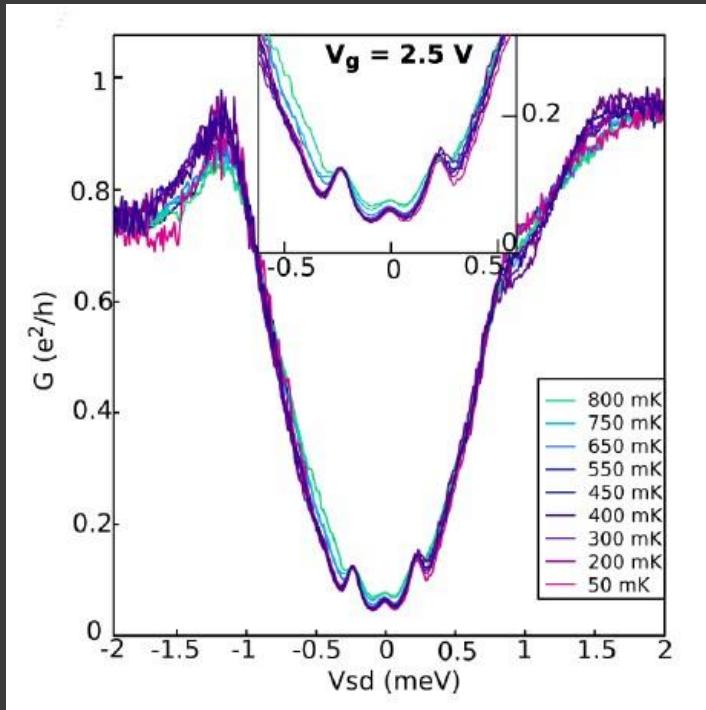
Zero-bias conductance peak



Zero-bias conductance peak



Zero-bias conductance peak



Summary

- Induced spin orbit coupling and Zeeman splitting by magnetic texture
- Oscillating subgap states (fingerprint of SOI)
- Zero-energy mode by tuning gate voltage (Majorana modes?)
- Possible without large external B-field

Thank you for your attention!